RC4580



RC4580 双通道音频运算放大器

1 特性

工作电压: ±2V 至 ±18V • 低噪声电压: 0.8 µ Vrms • 增益带宽积:12MHz • 总谐波失真: 0.0005%

• 压摆率:5V/µs

• NJM4580 的直接替代产品

• 与 LM833、NE5532、NJM4558/9 和 NJM4560/2/5 器件引脚和功能兼容

2 应用

音频前置放大器

有源滤波器

耳机放大器

工业测量设备

3 说明

RC4580 器件是一款双通道运算放大器,专为音频应用 (例如改进音调控制)而设计。该器件可提供低噪声、 高增益带宽、低谐波失真和高输出电流,专为前置放大 器、有源滤波器和工业测量设备等音频电子设备而设 计。当要求高输出电流时,可将 RC4580 器件用作耳 机放大器。RC4580 器件具有较宽的工作电源电压范 围,因此也可用于低压应用。

封装信息

器件型号	封装 ⁽¹⁾	本体尺寸 ⁽²⁾
	D (SOIC , 8)	3.9mm × 4.9mm
	P (PDIP , 8)	9.81mm × 9.43mm
RC4580	PW (TSSOP, 8)	3.0mm × 4.4mm
	DGK (VSSOP , 8)	3.0mm × 3.0mm
	DDF (SOT-23 , 8)	1.6mm × 2.9mm

- 有关所有可用封装,请参阅节10。
- 封装尺寸(长×宽)为标称值,并包括引脚(如适用)。

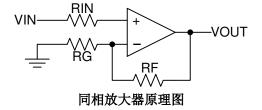




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4 Pin Configuration and Functions

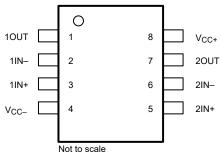


图 4-1. D, PW, and DGK Packages 8-Pin SOIC, TSSOP, and VSSOP (Top View)

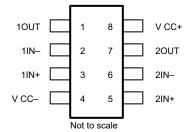


图 4-2. DDF Package 8-Pin SOT-23 (Top View)

表 4-1. Pin Functions

PIN		1/0	DESCRIPTION			
NAME	NO.	- 1/0	DESCRIPTION			
1IN+	3	I	Noninverting input			
1IN -	2	I	Inverting input			
10UT	1	0	Output			
2IN+	5	I	Noninverting input			
2IN -	6	I	Inverting input			
2OUT	7	0	Output			
V _{CC+}	8	_	Positive supply			
V _{CC} -	4	_	Negative supply			

3



5 Specifications

5.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted) (1)

		MIN	MAX	UNIT
V _{CC}	Supply voltage		±18	V
VI	Input voltage (any input)		±15	V
V _{ID}	Differential input voltage		±30	V
Io	Output current		±50	mA
T _A	Ambient temperature range	- 40	125	°C
T _{stg}	Storage temperature range	- 60	125	°C

⁽¹⁾ Operation outside the Absolute Maximum Ratings may cause permanent device damage. Absolute Maximum Ratings do not imply functional operation of the device at these or any other conditions beyond those listed under Recommended Operating Conditions. If used outside the Recommended Operating Conditions but within the Absolute Maximum Ratings, the device may not be fully functional, and this may affect device reliability, functionality, performance, and shorten the device lifetime.

5.2 ESD Ratings

			MIN	MAX	UNIT
,,	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001, all pins ⁽¹⁾	0	1000	V
V _(ESD)	Electrostatic discharge	Charged device model (CDM), per JEDEC specification JESD22-C101, all pins ⁽²⁾	0	1000	V

- (1) JEDEC document JEP155 states that 500V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250V CDM allows safe manufacturing with a standard ESD control process.

5.3 Recommended Operating Conditions

		MIN	MAX	UNIT
V _{CC+}	Supply voltage	2	16	V
V _{CC} -	Supply voltage		- 16	v
V _{ICR}	Input common-mode voltage range	- 13.5	13.5	V
T _A	Operating free-air temperature	- 40	125	°C

5.4 Thermal Information

				RC4580			
	THERMAL METRIC(1)	D (SOIC)	P (PDIP)	PW (TSSOP)	DGK (VSSOP)	DDF (SOT-23)	UNIT
		8 PINS	8 PINS	8 PINS	8 PINS	8 PINS	
R _{0 JA}	Junction-to-ambient thermal resistance	109	99.2	163	160.5	177.9	
R _θ JC(top)	Junction-to-case (top) thermal resistance	55.7	78.8	38	70.2	96.5	
R _{0 JB}	Junction-to-board thermal resistance	49	61.9	90.6	95.6	95.2	°C/W
ψ ЈТ	Junction-to-top characterization parameter	10.6	44.8	1.3	8.8	9.5	C/VV
ψ ЈВ	Junction-to-board characterization parameter	48.6	61.2	88.9	94.0	95.0	
R _θ JC(bot)	Junction-to-case (bottom) thermal resistance	_	_	_	_	_	

(1) For more information about traditional and new thermal metrics, see the Semiconductor IC Package Thermal Metrics application note.

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5.5 Electrical Characteristics

 $V_{CC\pm} = \pm 15 \text{ V}, T_A = -40^{\circ}\text{C} \text{ to } 125^{\circ}\text{C} \text{ (unless otherwise noted)}$

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
V _{IO}	Input offset voltage	R _S = < 10k Ω		0.5	3	mV
I _{IO}	Input offset current			5	200	nA
I _{IB}	Input bias current			100	500	nA
A _{VD}	Large-signal differential voltage amplification	$R_L \geqslant 2k \Omega$, $V_O = \pm 10V$	90	110		dB
V _{CM}	Output voltage swing	$R_L \geqslant 2k \Omega$	±12	±13.5		V
V _{ICR}	Common-mode input voltage		±12	±13.5		V
CMRR	Common-mode rejection ratio	$R_S \leqslant 10k\Omega$	80	110		dB
k _{SVR}	Supply-voltage rejection ratio ⁽¹⁾	$R_S \le 10k\Omega$	80	110		dB
I _{CC}	Total supply current (all amplifiers)			6	9	mA

(1) Measured with V_{CC±} varied simultaneously

5.6 Operating Characteristics

 $V_{CC\pm} = \pm 15 \text{ V}, T_A = -40^{\circ}\text{C} \text{ to } 125^{\circ}\text{C} \text{ (unless otherwise noted)}$

	PARAMETER	TEST CONDITIONS	TYP	UNIT
SR	Slew rate at unity gain	$R_L \geqslant 2k \Omega$	5	V/μs
GBW	Gain-bandwidth product	f = 10kHz	12	MHz
THD	Total harmonic distortion	$V_O = 5V$, $R_L = 2k \Omega$, $f = 1kHz$, $A_{VD} = 20dB$	0.0005%	
V _n	Equivalent input noise voltage	RIAA, $R_S \le 2.2 k \Omega$, 30kHz LPF	0.8	μ Vrms

5.7 Typical Characteristics

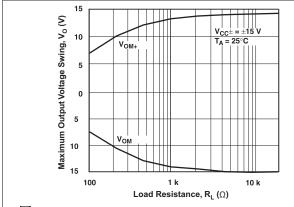


图 5-1. Maximum Output Voltage Swing vs Load Resistance

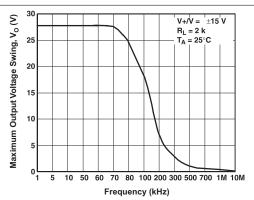
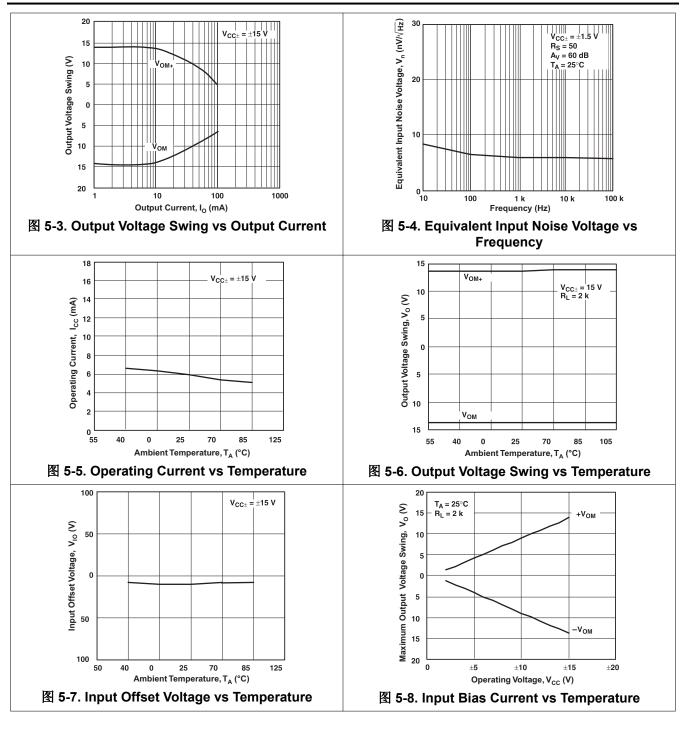


图 5-2. Maximum Ouput Voltage Swing vs Frequency





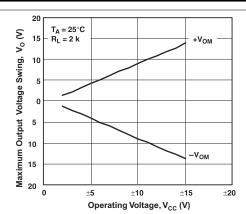


图 5-9. Maximum Output Voltage Swing vs Operating Voltage

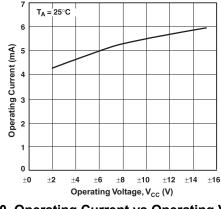


图 5-10. Operating Current vs Operating Voltage

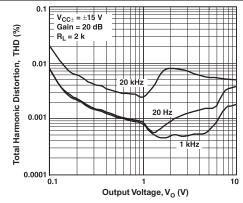


图 5-11. Total Harmonic Distortion vs Output Voltage

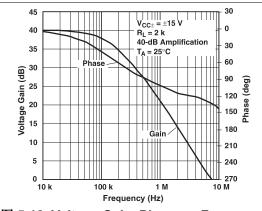


图 5-12. Voltage Gain, Phase vs Frequency

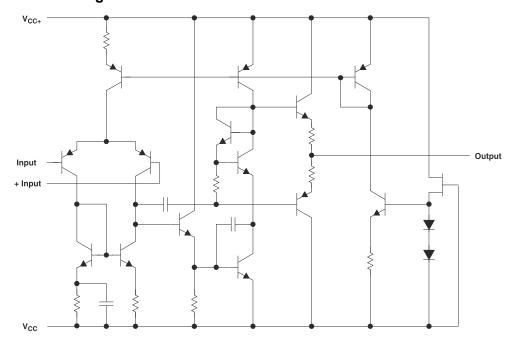


6 Detailed Description

6.1 Overview

The RC4580 device is a dual operational amplifier that has been designed optimally for audio applications, such as improving tone control. The device offers low noise, high gain bandwidth, low harmonic distortion, and high output current. When high output current is required, the RC4580 device can be used as a headphone amplifier. Due to the wide operating supply voltage of the device, the RC4580 device can also be used in low-voltage applications.

6.2 Functional Block Diagram



6.3 Feature Description

6.3.1 Unity-Gain Bandwidth

The unity-gain bandwidth is the frequency up to which an amplifier with a unity gain may be operated without greatly distorting the signal. The RC4580 device has a 12MHz unity-gain bandwidth.

6.3.2 Common-Mode Rejection Ratio

The common-mode rejection ratio (CMRR) of an amplifier is a measure of how well the device rejects unwanted input signals common to both input leads. The CMRR is found by taking the ratio of the change in input offset voltage to the change in the input voltage, then converting to decibels. Ideally the CMRR is infinite, but in practice, amplifiers are designed to have the CMRR as high as possible. The CMRR of the RC4580 device is 110dB.

6.3.3 Slew Rate

The slew rate is the rate at which an operational amplifier can change the op amp output when there is a change on the input. The RC4580 device has a 5V/µs slew rate.

6.4 Device Functional Mode

The RC4580 device is powered on when the supply is connected. Each device can operate as a single-supply operational amplifier or dual-supply amplifier depending on the application.

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7 Application and Implementation

备注

以下应用部分中的信息不属于 TI 器件规格的范围,TI 不担保其准确性和完整性。TI 的客 户应负责确定器件是否适用于其应用。客户应验证并测试其设计,以确保系统功能。

7.1 Typical Application

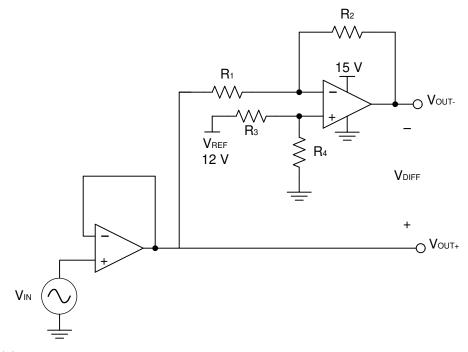


图 7-1. Schematic for Single-Ended Input to Differential Output Conversion

7.1.1 Design Requirements

The design requirements are as follows:

Supply voltage: 15VReference voltage: 12VInput: 2V to 10V

Output differential: ±8V

7.1.2 Detailed Design Procedure

The circuit in $\[\]$ 7-1 takes a single-ended input signal, V_{IN} , and generates two output signals, V_{OUT+} and V_{OUT-} using two amplifiers and a reference voltage, V_{REF} . V_{OUT+} is the output of the first amplifier and is a buffered version of the input signal, V_{IN} (see 方程式 1). V_{OUT-} is the output of the second amplifier which uses V_{REF} to add an offset voltage to V_{IN} and feedback to add inverting gain. The transfer function for V_{OUT-} is 5程式 2.

$$V_{OUT+} = V_{IN} \tag{1}$$

$$V_{\text{OUT-}} = V_{\text{REF}} \times \left(\frac{R_4}{R_3 + R_4}\right) \times \left(1 + \frac{R_2}{R_1}\right) - V_{\text{IN}} \times \frac{R_2}{R_1}$$
(2)

The differential output signal, V_{DIFF} , is the difference between the two single-ended output signals, V_{OUT+} and V_{OUT-} . 方程式 3 shows the transfer function for V_{DIFF} . By applying the conditions that $R_1 = R_2$ and $R_3 = R_4$, the transfer function is simplified into 方程式 6. Using this configuration, the maximum input signal is equal to the reference voltage and the maximum output of each amplifier is equal to the V_{REF} . The differential output range is $2 \times V_{REF}$. Furthermore, the common-mode voltage is one half of V_{REF} (see 5×10^{-2}).

$$V_{DIFF} = V_{OUT_{+}} - V_{OUT_{-}} = V_{IN} \times \left(1 + \frac{R_{2}}{R_{1}}\right) - V_{REF} \times \left(\frac{R_{4}}{R_{3} + R_{4}}\right) \left(1 + \frac{R_{2}}{R_{1}}\right)$$
(3)

$$V_{OUT+} = V_{IN} \tag{4}$$

$$V_{OUT-} = V_{REF} - V_{IN}$$
 (5)

$$V_{DIFF} = 2 \times V_{IN} - V_{RFF} \tag{6}$$

$$V_{cm} = \left(\frac{V_{OUT+} + V_{OUT-}}{2}\right) = \frac{1}{2}V_{REF}$$
(7)

7.1.2.1 Amplifier Selection

Linearity over the input range is key for good DC accuracy. The common-mode input range and the output swing limitations determine the linearity. In general, an amplifier with rail-to-rail input and output swing is required. Bandwidth is a key concern for this design. The RC4580 device has a bandwidth of 12MHz, therefore this circuit is only be able to process signals with frequencies of less than 12MHz.

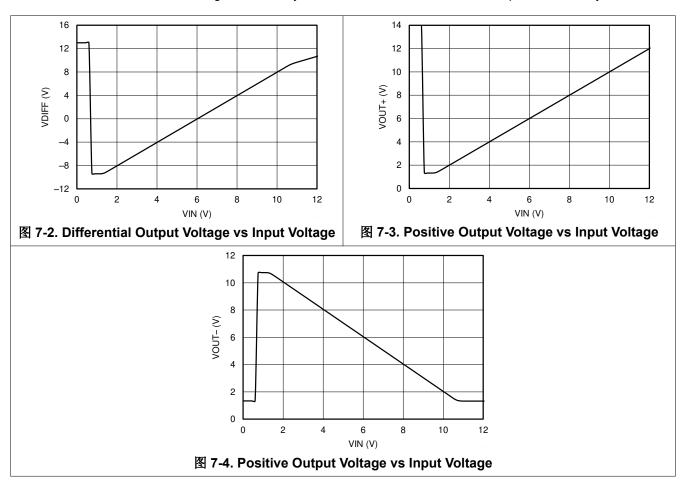
7.1.2.2 Passive Component Selection

Because the transfer function of V_{OUT} is heavily reliant on resistors (R_1 , R_2 , R_3 , and R_4), use resistors with low tolerances to maximize performance and minimize error. This design used resistors with resistance values of $36k\,\Omega$ with tolerances measured to be within 2%. But, if the noise of the system is a key parameter, the user can select smaller resistance values ($6k\,\Omega$ or lower) to keep the overall system noise low. This ensures that the noise from the resistors is lower than the amplifier noise.

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7.1.3 Application Curves

The measured transfer functions in № 7-2, № 7-3, and № 7-4 were generated by sweeping the input voltage from 0V to 12V. However, this design should only be used between 2V and 10V for optimum linearity.



7.2 Power Supply Recommendations

The RC4580 device is specified for operation over the range of ±2V to ±16V; many specifications apply from -40°C to 125°C. The *Typical Characteristics* section presents parameters that can exhibit significant variance with regard to operating voltage or temperature.

小心

Supply voltages outside of the ±18V range can permanently damage the device (see the *Absolute Maximum Ratings*).

Place $0.1 \,\mu$ F bypass capacitors close to the power-supply pins to reduce errors coupling in from noisy or high impedance power supplies. For more detailed information on bypass capacitor placement, refer to the *Layout Guidelines*.

Product Folder Links: RC4580

7.3 Layout

7.3.1 Layout Guidelines

For best operational performance of the device, use good PCB layout practices, including:

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- Noise can propagate into analog circuitry through the power pins of the circuit as a whole and the operational amplifier. Bypass capacitors are used to reduce the coupled noise by providing low impedance power sources local to the analog circuitry.
 - Connect low-ESR, 0.1 μ F ceramic bypass capacitors between each supply pin and ground, placed as close to the device as possible. A single bypass capacitor from V+ to ground is applicable for single supply applications.
- Separate grounding for analog and digital portions of circuitry is one of the simplest and most-effective methods of noise suppression. One or more layers on multilayer PCBs are usually devoted to ground planes. A ground plane helps distribute heat and reduces EMI noise pickup.
- To reduce parasitic coupling, run the input traces as far away from the supply or output traces as possible. If it is not possible to keep them separate, it is much better to cross the sensitive trace perpendicular as opposed to in parallel with the noisy trace.
- Place the external components as close to the device as possible. Keeping RF and RG close to the inverting input minimizes parasitic capacitance, as shown in *Layout Example*.
- Keep the length of input traces as short as possible. Always remember that the input traces are the most sensitive part of the circuit.
- Consider a driven, low-impedance guard ring around the critical traces. A guard ring can significantly reduce leakage currents from nearby traces that are at different potentials.

7.3.2 Layout Example

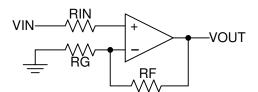


图 7-5. Operational Amplifier Schematic for Noninverting Configuration

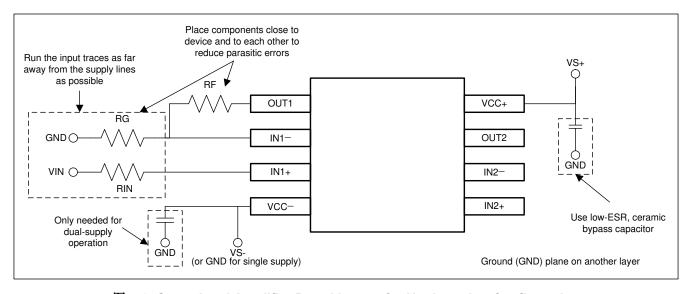


图 7-6. Operational Amplifier Board Layout for Noninverting Configuration

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8 Device and Documentation Support

8.1 接收文档更新通知

要接收文档更新通知,请导航至 ti.com 上的器件产品文件夹。点击*通知* 进行注册,即可每周接收产品信息更改摘 要。有关更改的详细信息,请查看任何已修订文档中包含的修订历史记录。

8.2 支持资源

TI E2E™ 中文支持论坛是工程师的重要参考资料,可直接从专家处获得快速、经过验证的解答和设计帮助。搜索 现有解答或提出自己的问题,获得所需的快速设计帮助。

链接的内容由各个贡献者"按原样"提供。这些内容并不构成 TI 技术规范,并且不一定反映 TI 的观点;请参阅 TI的使用条款。

8.3 Trademarks

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8.4 静电放电警告



静电放电 (ESD) 会损坏这个集成电路。德州仪器 (TI) 建议通过适当的预防措施处理所有集成电路。如果不遵守正确的处理 和安装程序,可能会损坏集成电路。

ESD 的损坏小至导致微小的性能降级,大至整个器件故障。精密的集成电路可能更容易受到损坏,这是因为非常细微的参 数更改都可能会导致器件与其发布的规格不相符。

8.5 术语表

TI术语表

本术语表列出并解释了术语、首字母缩略词和定义。

9 Revision History

•	Changes from Revision D (November 2014) to Revision E (November 2024)	Page
•	更新了整个文档中的表格、图和交叉参考的编号格式	1
•	向数据表中添加了 P (PDIP , 8) 和 DDF (SOT-23 , 8) 封装	1
•	Changed the slew rate value listed in the <i>Slew Rate</i> section from: 5V/ms to: 5V/µs to match the slew values listed in the <i>Features</i> section and <i>Electrical Characteristics</i> table	
•	Deleted references to the Circuit Board Layout Techniques application note	11
_	No. 11 Company	D
_	Changes from Revision C (March 2004) to Revision D (November 2014)	Page
_	添加了应用、器件信息表、引脚功能表、处理等级表、特性说明部分、器件功能模式、应用和实	完施 部分、电
_	, , , , , , , , , , , , , , , , , , , ,	完施 部分、电
•	添加了应用、器件信息表、引脚功能表、处理等级表、特性说明部分、器件功能模式、应用和实	<i>京施</i> 部分、 <i>电</i>
•	添加了 <i>应用、器件信息</i> 表、 <i>引脚功能</i> 表、 <i>处理等级</i> 表、 <i>特性说明</i> 部分、 <i>器件功能模式、应用和实源相关建议</i> 部分、 <i>布局</i> 部分、 <i>器件和文档支持</i> 部分以及 <i>机械、封装和可订购信息</i> 部分 删除了 <i>订购信息</i> 表	<i>E施</i> 部分、 <i>电</i> 1 1 table and
•	添加了 <i>应用、器件信息</i> 表、 <i>引脚功能</i> 表、 <i>处理等级</i> 表、特性说明部分、器件功能模式、应用和实源相关建议部分、布局部分、器件和文档支持部分以及机械、封装和可订购信息部分	<i>E施</i> 部分、 <i>电</i> 1 1 table and

10 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

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www.ti.com 3-May-2025

PACKAGING INFORMATION

Orderable part number	Status	Material type	Package Pins	Package qty Carrier	RoHS	Lead finish/ Ball material	MSL rating/ Peak reflow	Op temp (°C)	Part marking
part number	(1)	(2)			(3)	(4)	(5)		(6)
RC4580ID	Obsolete	Production	SOIC (D) 8	-	-	Call TI	Call TI	-40 to 125	R4580I
RC4580IDDFR	Active	Production	SOT-23-THIN (DDF) 8	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	4580F
RC4580IDGKR	Active	Production	VSSOP (DGK) 8	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	4580
RC4580IDR	Active	Production	SOIC (D) 8	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	R4580I
RC4580IP	Active	Production	PDIP (P) 8	50 TUBE	Yes	NIPDAU	N/A for Pkg Type	-40 to 125	RC4580IP
RC4580IPW	Obsolete	Production	TSSOP (PW) 8	-	-	Call TI	Call TI	-40 to 125	R4580I
RC4580IPWR	Active	Production	TSSOP (PW) 8	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	R4580I

⁽¹⁾ Status: For more details on status, see our product life cycle.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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⁽²⁾ Material type: When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

⁽³⁾ RoHS values: Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

⁽⁴⁾ Lead finish/Ball material: Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

⁽⁵⁾ MSL rating/Peak reflow: The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

⁽⁶⁾ Part marking: There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

PACKAGE OPTION ADDENDUM

www.ti.com 3-May-2025

OTHER QUALIFIED VERSIONS OF RC4580:

Automotive : RC4580-Q1

NOTE: Qualified Version Definitions:

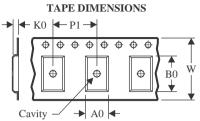
• Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects



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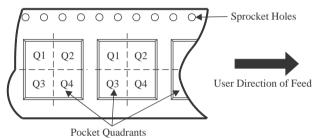
TAPE AND REEL INFORMATION





	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
RC4580IDDFR	SOT-23- THIN	DDF	8	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
RC4580IDGKR	VSSOP	DGK	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
RC4580IDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
RC4580IDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
RC4580IPWR	TSSOP	PW	8	2000	330.0	12.4	7.0	3.6	1.6	8.0	12.0	Q1



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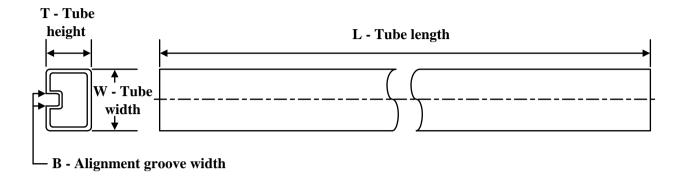
*All dimensions are nominal

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Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
RC4580IDDFR	SOT-23-THIN	DDF	8	3000	210.0	185.0	35.0
RC4580IDGKR	VSSOP	DGK	8	2500	356.0	356.0	35.0
RC4580IDR	SOIC	D	8	2500	353.0	353.0	32.0
RC4580IDR	SOIC	D	8	2500	356.0	356.0	35.0
RC4580IPWR	TSSOP	PW	8	2000	356.0	356.0	35.0

PACKAGE MATERIALS INFORMATION

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TUBE

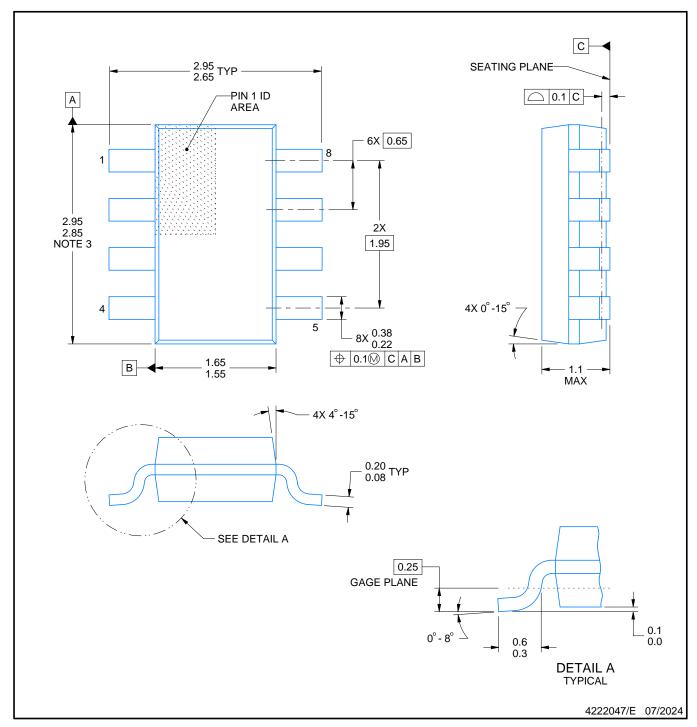


*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
RC4580IP	Р	PDIP	8	50	506	13.97	11230	4.32



PLASTIC SMALL OUTLINE



NOTES:

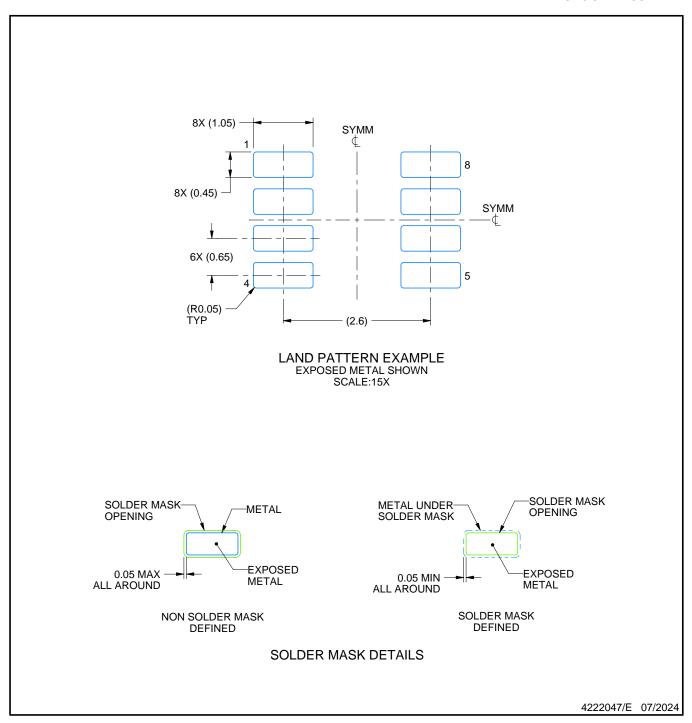
- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.



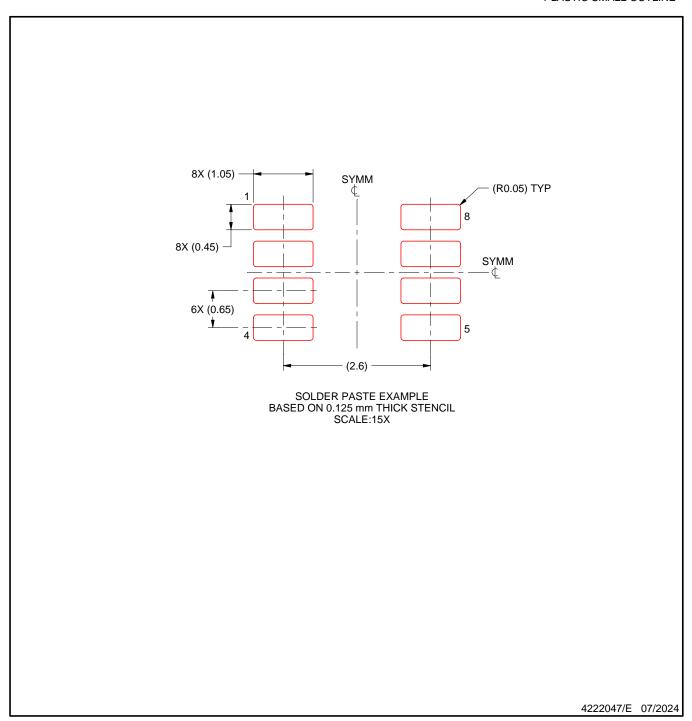
PLASTIC SMALL OUTLINE



- 4. Publication IPC-7351 may have alternate designs.
- 5. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



PLASTIC SMALL OUTLINE



- 6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 7. Board assembly site may have different recommendations for stencil design.





SMALL OUTLINE INTEGRATED CIRCUIT



NOTES:

- 1. Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.
- 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 [0.15] per side.
- 4. This dimension does not include interlead flash.
- 5. Reference JEDEC registration MS-012, variation AA.



SMALL OUTLINE INTEGRATED CIRCUIT



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE INTEGRATED CIRCUIT

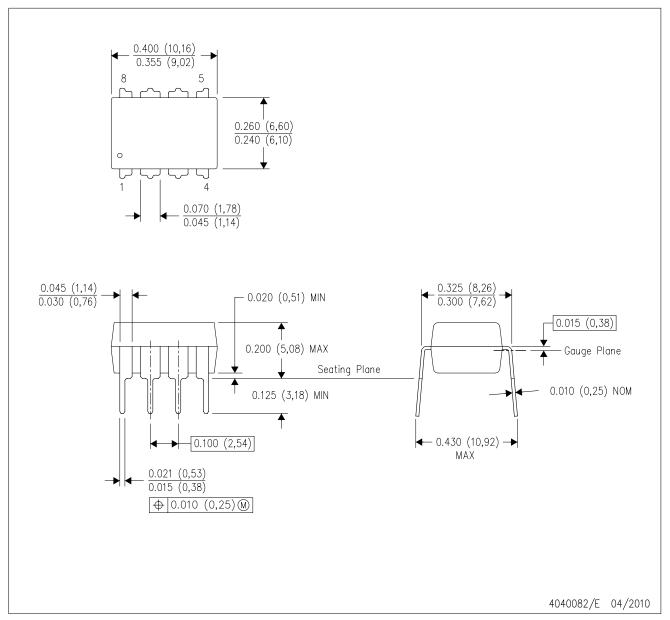


- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



P (R-PDIP-T8)

PLASTIC DUAL-IN-LINE PACKAGE

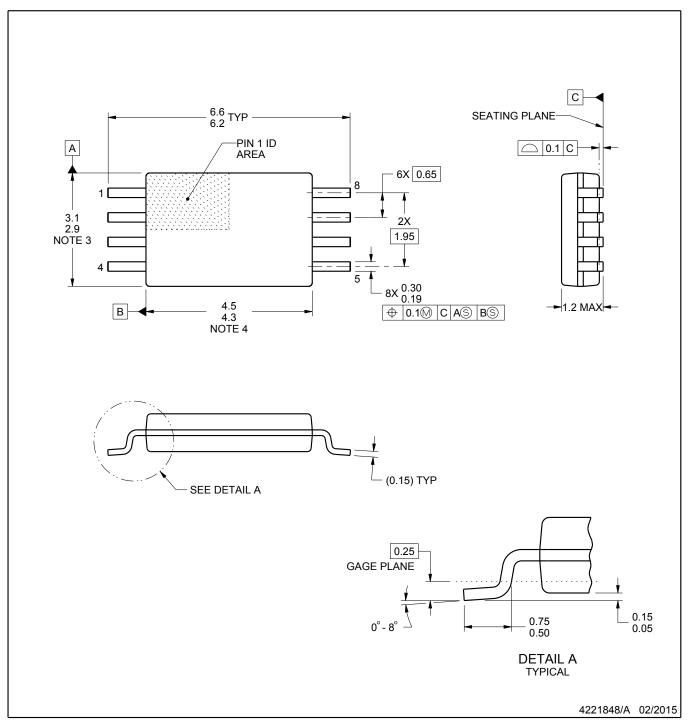


NOTES:

- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- C. Falls within JEDEC MS-001 variation BA.







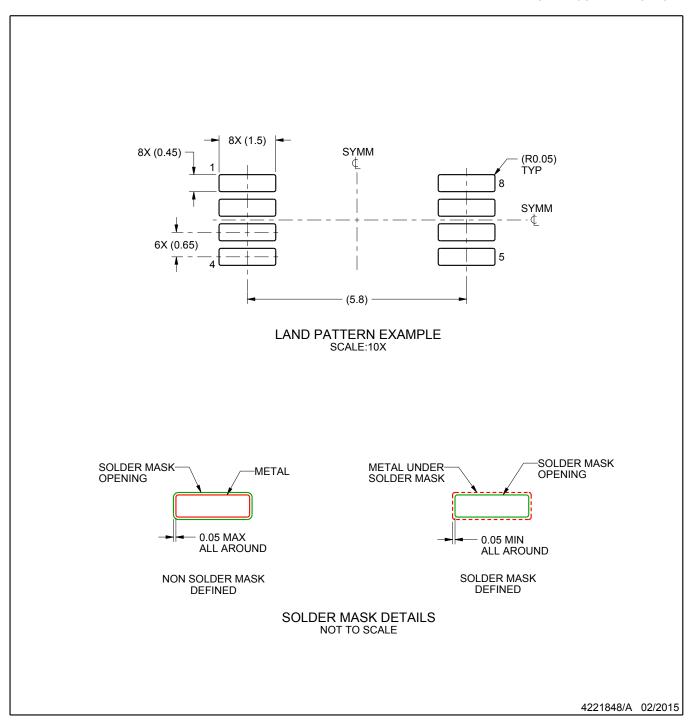
NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-153, variation AA.



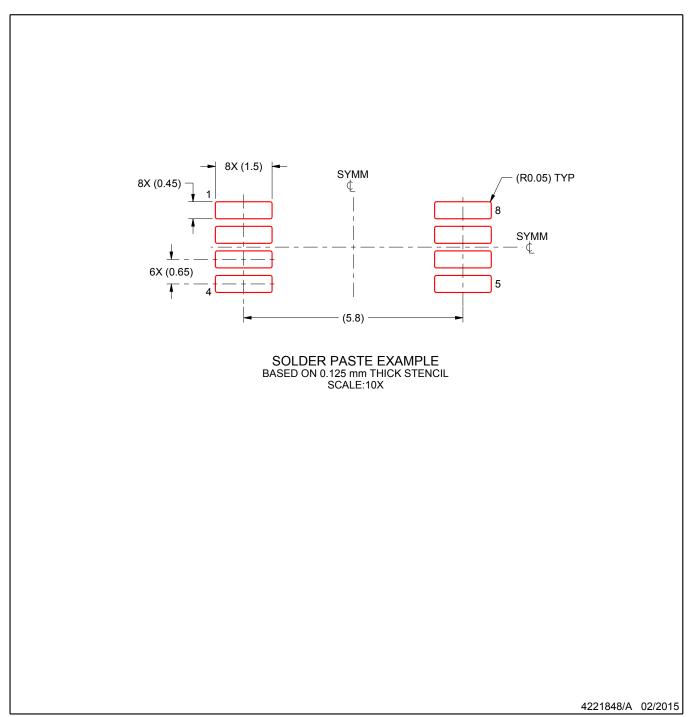


NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

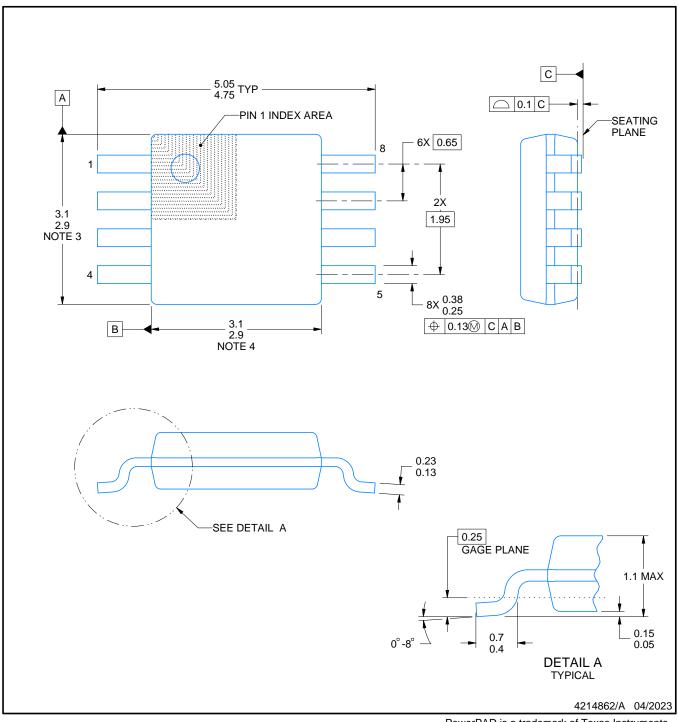




- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.







NOTES:

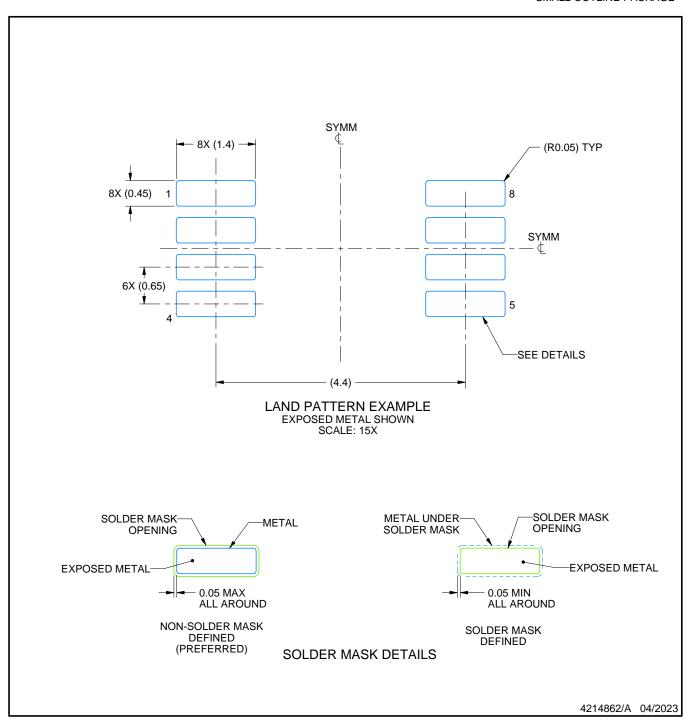
PowerPAD is a trademark of Texas Instruments.

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

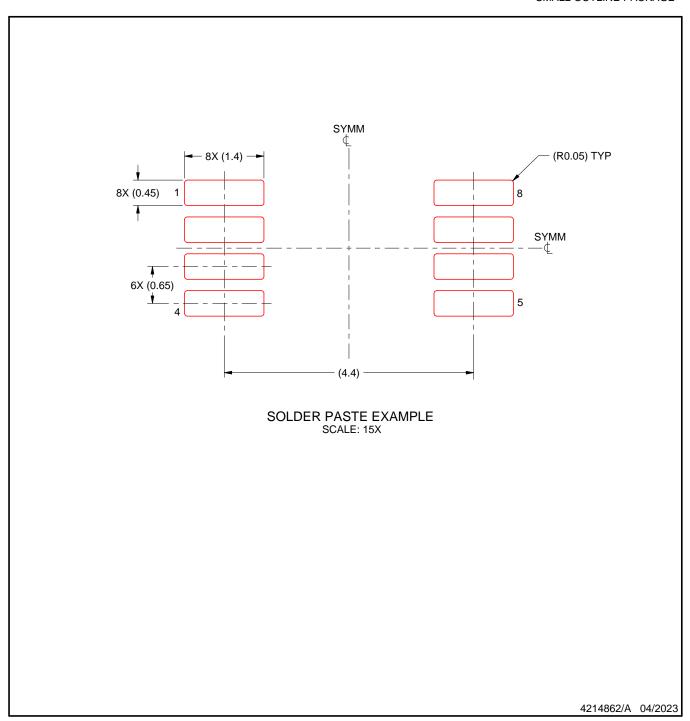
 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-187.





- 6. Publication IPC-7351 may have alternate designs.
- 7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.
- 8. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.
- 9. Size of metal pad may vary due to creepage requirement.





- 11. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 12. Board assembly site may have different recommendations for stencil design.



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